

LISTING OF THE CLAIMS:

Claim 1 (Currently Amended): An anode thin film for a lithium secondary battery ~~having~~ comprising a current collector and an anode active material layer ~~formed thereon~~ arranged above the current collector, wherein the anode active material layer is a multiple-layer thin film comprising a silicon (Si) layer and a silver (Ag) layer,

further comprising a buffer layer between the current collector and the anode active material layer, the buffer layer being made of at least one selected from the group consisting of vanadium, nickel, molybdenum and copper.

Claim 2 (Canceled)

Claim 3 (Currently Amended): The anode thin film of claim 1, ~~2~~, wherein the thickness of the buffer layer is in the range of 50 to 250 Å.

Claim 4 (Original): The anode thin film of claim 1, wherein the thickness of the Si layer is in the range of 50 to 250 Å and the thickness of the Ag layer is in the range of 10 to 70 Å.

Claim 5 (Original): The anode thin film of claim 1, wherein the Si layer and the Ag layer are alternately stacked.

Claim 6 (Original): The anode thin film of claim 5, wherein the Ag layer is formed between Si layers.

Claim 7 (Original): The anode thin film of claim 1, wherein the topmost layer of the multiple-layer thin film is made of Ag.

Claim 8 (Currently Amended): An anode thin film for a lithium secondary battery comprising having a current collector and an anode active material layer ~~formed thereon~~ arranged above the current collector, wherein the anode active material layer is a single-layer thin film comprising silicon (Si) and silver (Ag),

further comprising a buffer layer between the current collector and the anode active material layer, the buffer layer comprising a horizontal layer being made of at least one selected from the group consisting of vanadium, nickel, molybdenum and copper.

Claim 9 (Original): The anode thin film of claim 8, wherein Si and Ag comprised in the single layer are mixed in a molar ratio of 7:3 to 3:7.

Claim 10 (Canceled)

Claim 11 (New): The anode thin film of claim 8, wherein the thickness of the buffer layer is in the range of 50 to 250 Å.

Claim 12 (New): The anode thin film of claim 8, wherein the entire anode active material layer is arranged above the buffer layer.

Claim 13 (New): The anode thin film of claim 8, wherein the entire buffer layer is arranged above the current collector.

Claim 14 (New): The anode thin film of claim 1, wherein the silicon layer consists of silicon.

Claim 15 (New): The anode thin film of claim 1, wherein the silver layer consists of silver.